

N-channel 60V, 7.5mΩ, 80A, TO-263 Trench Power MOSFET 溝槽式功率場效應管

■ Features 特點

Advanced trench technology 優秀溝槽技術

Ultra low on-resistance 超低導通電阻

Low gate charge 低柵電荷密度

Fast switching 快速開關能力

■ Applications 應用

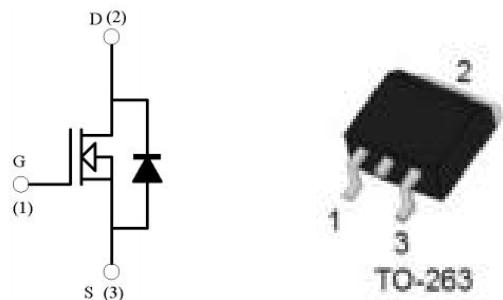
Switch mode power supplies 開關電源

DC-DC converters and UPS 直流直流變換和不斷電系統

PWM motor controls 脉寬調制電機控制

General switching applications 普通開關應用

■ Internal Schematic Diagram 內部結構



■ Absolute Maximum Ratings 最大額定值

Characteristic 特性參數	Symbol 符號	Rat 額定值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	BV_{DSS}	60	V
Gate- Source Voltage 柵極-源極電壓	V_{GS}	± 20	V
Drain Current (continuous)漏極電流 - 連續	I_D (at $TC = 25^\circ C$) at $TC = 100^\circ C$)	80 55	A
Drain Current (pulsed)漏極電流 - 脉冲	I_{DM}	300	A
Total Device Dissipation 總耗散功率	P_{TOT} (at $TC = 25^\circ C$)	108	W
Single Pulse Avalanche Energy 雪崩能量	E_{AS}	380*	mJ
Thermal Resistance Junction-Case 热阻	$R_{\Theta JC}$	1.3	°C/W
Junction/Storage Temperature 結溫/儲存溫度	T_J, T_{stg}	-55~175	°C

* E_{AS} condition : $L=0.5mH$, $R_g=25\Omega$, $V_D=30V$, $V_{GS}=10V$, I_D rating 20A

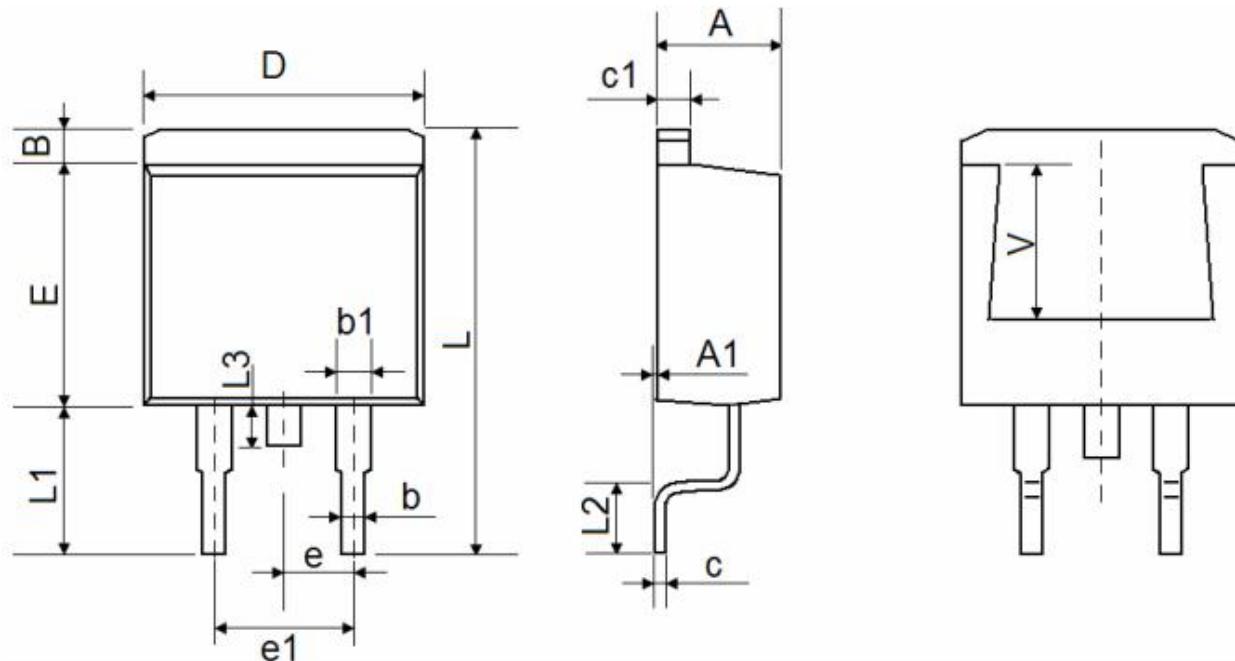
■ Electrical Characteristics 電特性

($T_A=25^\circ\text{C}$ unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓($I_D=250\mu\text{A}, V_{GS}=0\text{V}$)	BV_{DSS}	60	—	—	V
Gate Threshold Voltage 柵極開啓電壓($I_D=250\mu\text{A}, V_{GS}=V_{DS}$)	$V_{GS(\text{th})}$	1	1.7	2.5	V
Zero Gate Voltage Drain Current 零柵壓漏極電流($V_{GS}=0\text{V}, V_{DS}=60\text{V}$)	I_{DSS}	—	—	1	μA
Gate Body Leakage 柵極漏電流($V_{GS}=\pm20\text{V}, V_{DS}=0\text{V}$)	I_{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源導通電阻($I_D=30\text{A}, V_{GS}=10\text{V}$) ($I_D=20\text{A}, V_{GS}=4.5\text{V}$)	$R_{\text{DS}(\text{ON})}$	—	7.5 10	10 14	$\text{m}\Omega$
Diode Forward Voltage Drop 內附二極管正向壓降($I_{SD}=20\text{A}, V_{GS}=0\text{V}$)	V_{SD}	—	—	1.2	V
Forward Transfer Admittance 正向傳輸導納($V_{DS}=5\text{V}, I_D=20\text{A}$)	G_{FS}	20	—	—	S
Input Capacitance 輸入電容 ($V_{GS}=0\text{V}, V_{DS}=30\text{V}, f=1\text{MHz}$)	C_{ISS}	—	3800	—	pF
Common Source Output Capacitance 共源輸出電容($V_{GS}=0\text{V}, V_{DS}=30\text{V}, f=1\text{MHz}$)	C_{OSS}	—	280	—	pF
Reverse Transfer Capacitance 回饋電容($V_{GS}=0\text{V}, V_{DS}=30\text{V}, f=1\text{MHz}$)	C_{RSS}	—	200	—	pF
Total Gate Charge 柵極電荷密度 ($V_{DS}=30\text{V}, I_D=30\text{A}, V_{GS}=10\text{V}$)	Q_g	—	90	—	nC
Gate Source Charge 柵源電荷密度 ($V_{DS}=30\text{V}, I_D=30\text{A}, V_{GS}=10\text{V}$)	Q_{gs}	—	9	—	nC
Gate Drain Charge 柵漏電荷密度 ($V_{DS}=30\text{V}, I_D=30\text{A}, V_{GS}=10\text{V}$)	Q_{gd}	—	18	—	nC
Turn-On Delay Time 開啓延遲時間 ($V_{DS}=30\text{V}, I_D=3.5\text{A}, R_{\text{GEN}}=3\Omega, V_{GS}=10\text{V}$)	$t_{d(\text{on})}$	—	9	—	ns
Turn-On Rise Time 開啓上升時間 ($V_{DS}=30\text{V}, I_D=3.5\text{A}, R_{\text{GEN}}=3\Omega, V_{GS}=10\text{V}$)	t_r	—	8	—	ns
Turn-Off Delay Time 關斷延遲時間 ($V_{DS}=30\text{V}, I_D=3.5\text{A}, R_{\text{GEN}}=3\Omega, V_{GS}=10\text{V}$)	$t_{d(\text{off})}$	—	42	—	ns
Turn-On Fall Time 開啓下降時間 ($V_{DS}=30\text{V}, I_D=3.5\text{A}, R_{\text{GEN}}=3\Omega, V_{GS}=10\text{V}$)	t_f	—	16	—	ns

■ Dimension 外形封裝尺寸

T0-263



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	